IV2Q06060L1 – 650V 60mΩ Gen2 SiC MOSFET

Features

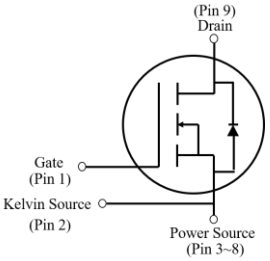
- 2nd Generation SiC MOSFET Technology with +18V gate drive
- High blocking voltage with low on-resistance
- High speed switching with low capacitance
- High operating junction temperature capability
- Very fast and robust intrinsic body diode
- Kelvin gate input easing driver circuit design

Applications

- Motor drivers
- Solar inverters
- Automotive DC/DC converters
- Automotive compressor inverters
- Switch mode power supplies

Outline:

TOLL



Marking Diagram:

2Q06060L1
YYWWZ
XXXX

2Q06060L1 = Specific Device Code
YY = Year
WW = Work Week
Z = Assembly Location
XXXX = Lot Traceability

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DS}	Drain-Source voltage	650	V	V_{GS}=0V, I_D=100μA	
V_{GSmax} (DC)	Maximum DC voltage	-5 to 20	V	Static (DC)	
V_{GSmax} (Spike)	Maximum spike voltage	-10 to 23	V	Duty cycle<1%, and pulse width<200ns	
V_{GSon}	Recommended turn-on voltage	18±0.5	V		
V_{GSoff}	Recommended turn-off voltage	-3.5 to -2	V		
I_D	Drain current (continuous)	43	A	V_{GS}=18V, T_C=25°C	Fig. 21
		32	A	V_{GS}=18V, T_C=100°C	
I_{DM}	Drain current (pulsed)	108	A	Pulse width limited by SOA	Fig. 24
P_{TOT}	Total power dissipation	174	W	T_C=25°C	Fig. 22
T_{stg}	Storage temperature range	-55 to 175	°C		
T_J	Operating junction temperature	-55 to 175	°C		
T_L	Solder Temperature	260	°C	wave soldering only allowed at leads, 1.6mm from case for 10 s	

Thermal Data

Symbol	Parameter	Value	Unit	Note
$R_{\theta(J-C)}$	Thermal Resistance from Junction to Case	0.86	°C/W	Fig. 23

Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
I_{DSS}	Zero gate voltage drain current		3	100	μA	V_{DS}=650V, V_{GS}=0V	
I_{GSS}	Gate leakage current			±100	nA	V_{DS}=0V, V_{GS}=-5~20V	
V_{TH}	Gate threshold voltage	1.8	2.8	4.5	V	V_{GS}=V_{DS}, I_D=5mA	Fig. 8, 9
			2.0			V_{GS}=V_{DS}, I_D=5mA @ T_J=175°C	
R_{ON}	Static drain-source on-resistance		60	78	mΩ	V_{GS}=18V, I_D=15A @T_J=25°C	Fig. 4, 5, 6, 7
			84		mΩ	V_{GS}=18V, I_D=15A @T_J=175°C	
C_{iss}	Input capacitance		1218		pF	V_{DS}=600V, V_{GS}=0V, f=1MHz, V_{AC}=25mV	Fig. 16
C_{oss}	Output capacitance		118		pF		
C_{rss}	Reverse transfer capacitance		7.6		pF		
E_{oss}	C_{oss} stored energy		24.6		μJ		Fig. 17
Q_g	Total gate charge		64		nC	V_{DS}=400V, I_D=15A, V_{GS}=-3 to 18V	Fig. 18
Q_{gs}	Gate-source charge		14		nC		
Q_{gd}	Gate-drain charge		33		nC		
R_g	Gate input resistance		4.7		Ω	f=1MHz	
E_{ON}	Turn-on switching energy		76.2		μJ	V_{DS}=400V, I_D=15A, V_{GS}=-3.5 to 18V, $R_{G(ext)}$=3.3Ω, L=200μH T_J=25°C	Fig. 19, 20
E_{OFF}	Turn-off switching energy		12.9		μJ		
$t_{d(on)}$	Turn-on delay time		4.3		ns		
t_r	Rise time		12.2				
$t_{d(off)}$	Turn-off delay time		11.4				
t_f	Fall time		7.8				

Reverse Diode Characteristics (T_C=25°C unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
V_{SD}	Diode forward voltage		4.2		V	I_{SD}=15A, V_{GS}=0V	Fig. 10, 11, 12
			3.9		V	I_{SD}=15A, V_{GS}=0V, T_J=175°C	
t_{rr}	Reverse recovery time		26.4		ns	V_{GS}=-3.5V/+18V, I_{SD}=15A, V_R=400V, $R_{G(ext)}$=13Ω L=200μH di/dt=3000A/μs	
Q_{rr}	Reverse recovery charge		138.5		nC		
I_{RRM}	Peak reverse recovery current		14.9		A		

Typical Performance (curves)

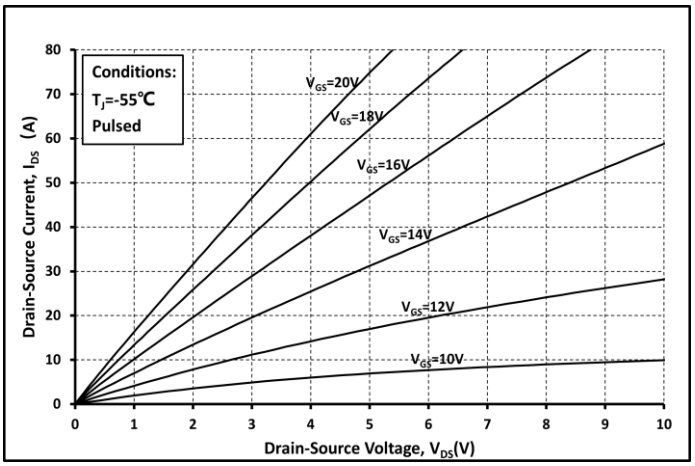


Fig. 1 Output Curve @ T_J=-55℃

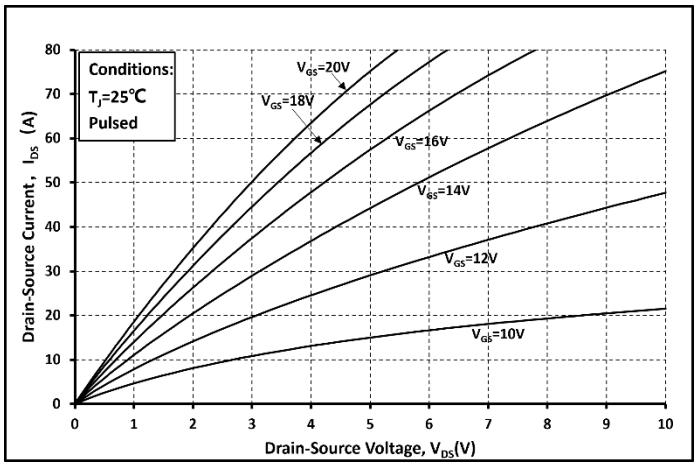


Fig. 2 Output Curve @ T_J=25℃

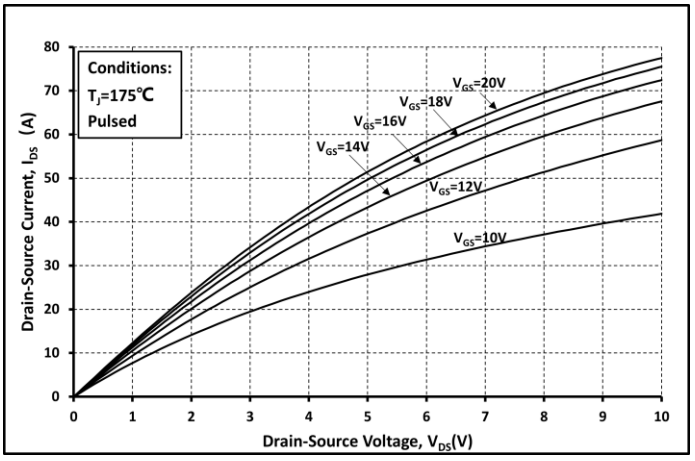


Fig. 3 Output Curve @ T_J=175℃

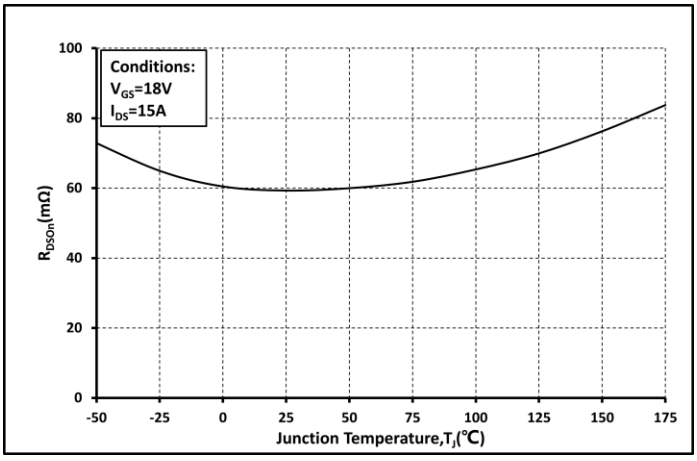


Fig. 4 Ron vs. Temperature

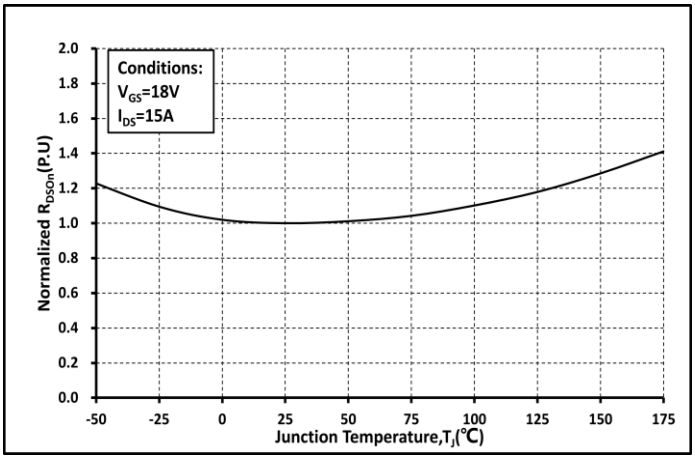


Fig. 5 Normalized Ron vs. Temperature

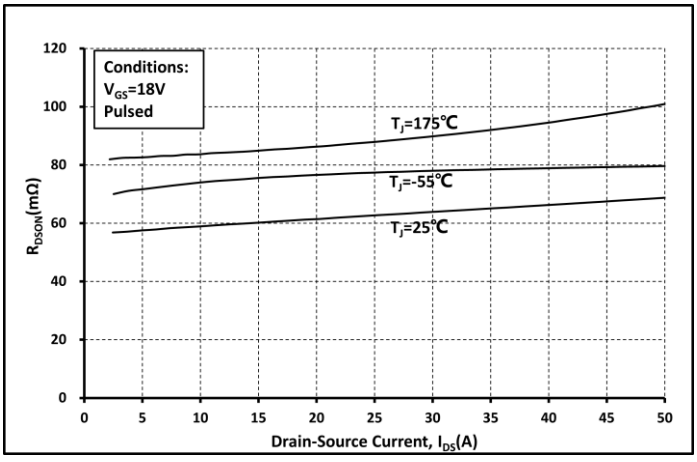


Fig. 6 Ron vs. I_{DS} @ Various Temperature

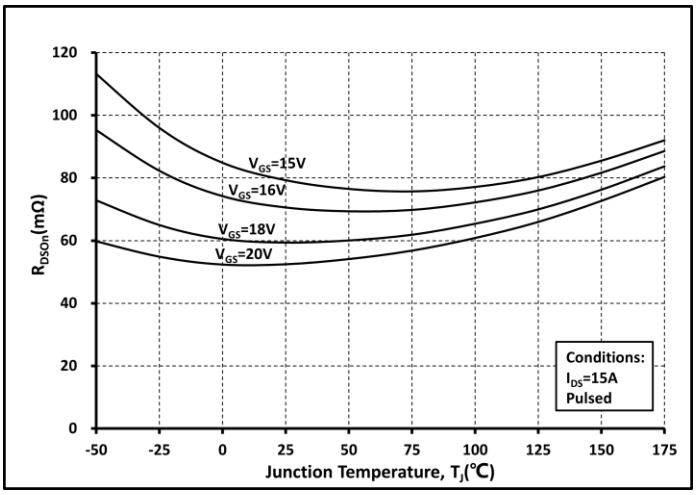


Fig. 7 Ron vs. Temperature @ Various V_{GS}

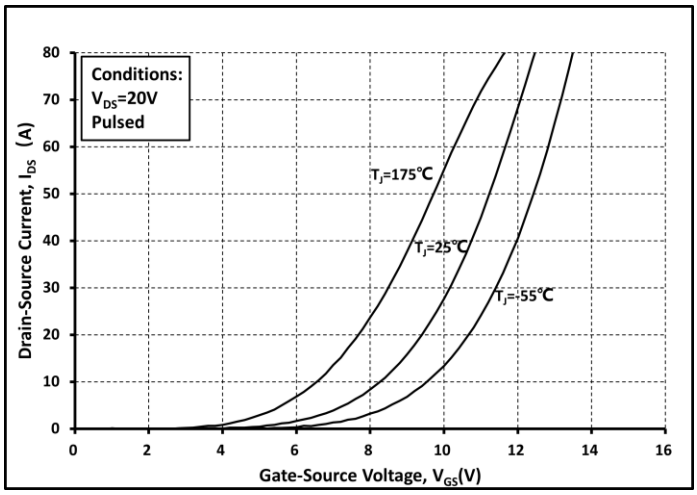


Fig. 8 Transfer Curves @ Various Temperature

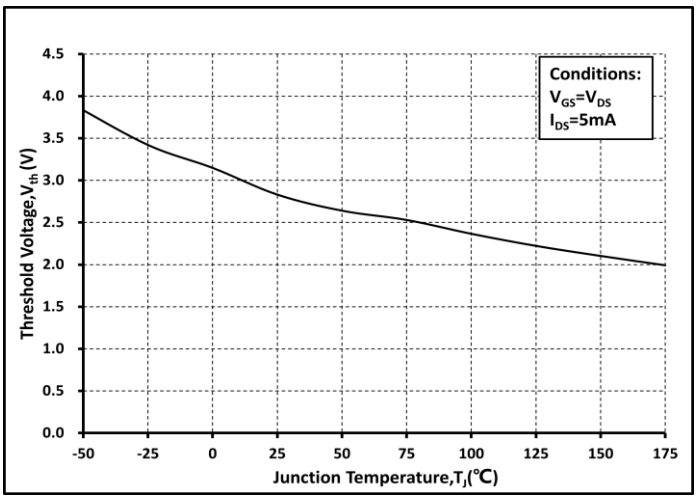


Fig. 9 Threshold Voltage vs. Temperature

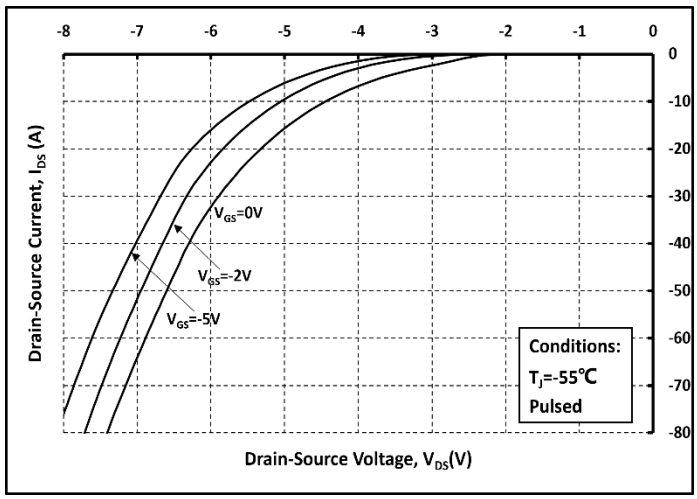


Fig. 10 Body Diode curves @ T_J=-55℃

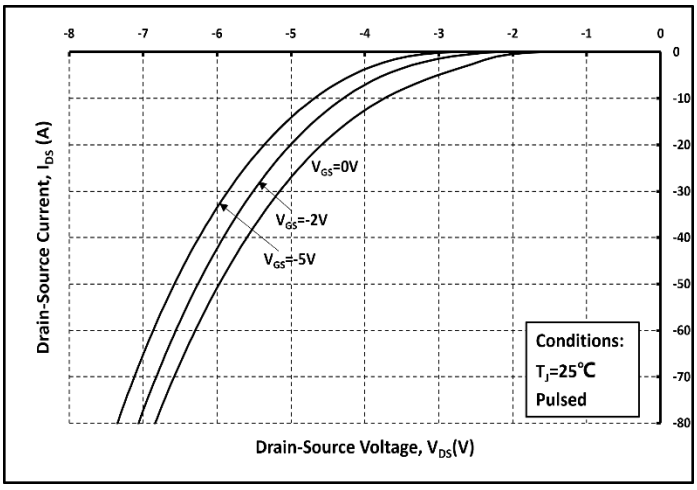


Fig. 11 Body Diode curves @ T_J=25℃

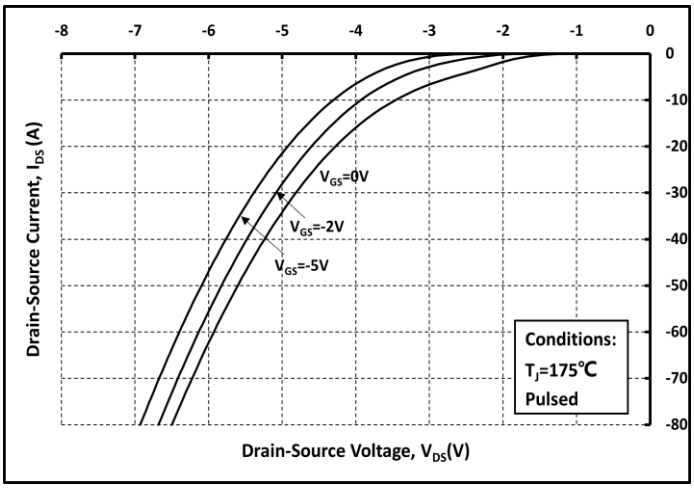


Fig. 12 Body Diode curves @ T_J=175℃

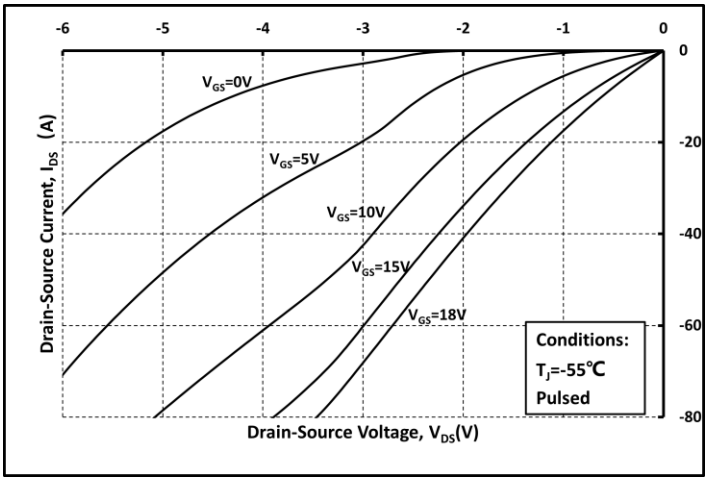


Fig. 13 3rd Quadrant curves @ T_J=-55°C

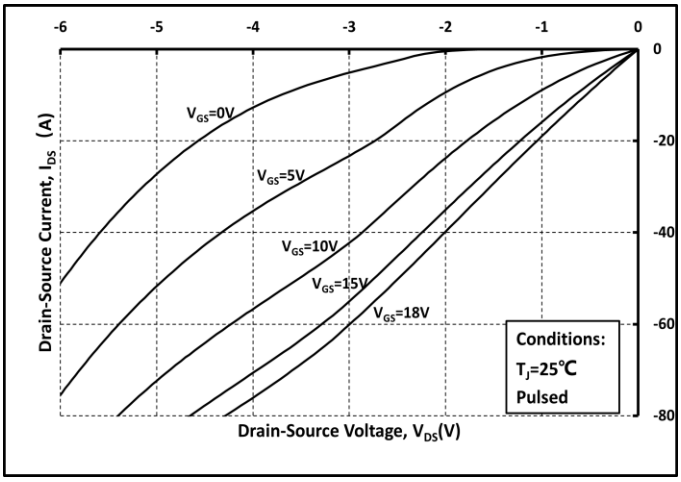


Fig. 14 3rd Quadrant curves @ T_J=25°C

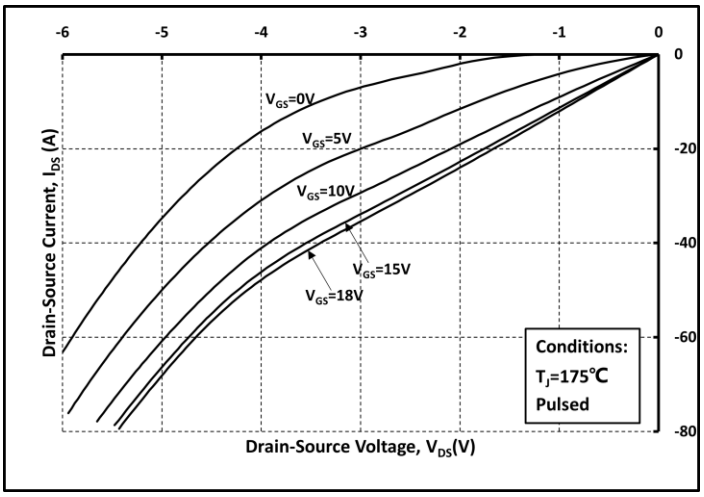


Fig. 15 3rd Quadrant curves @ T_J=175°C

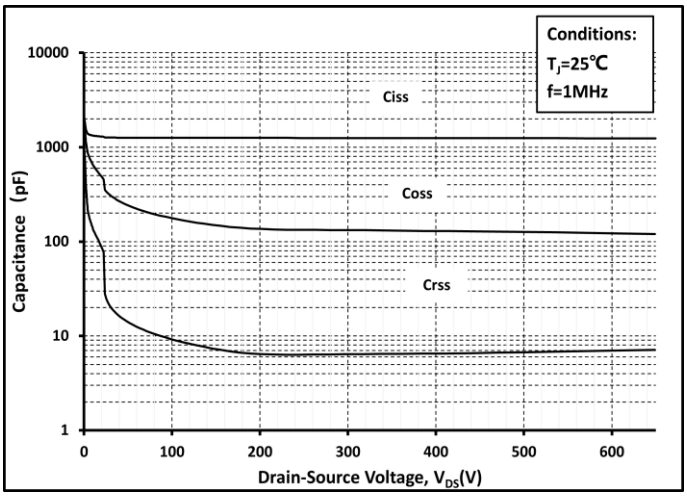


Fig. 16 Capacitance vs. V_{DS}

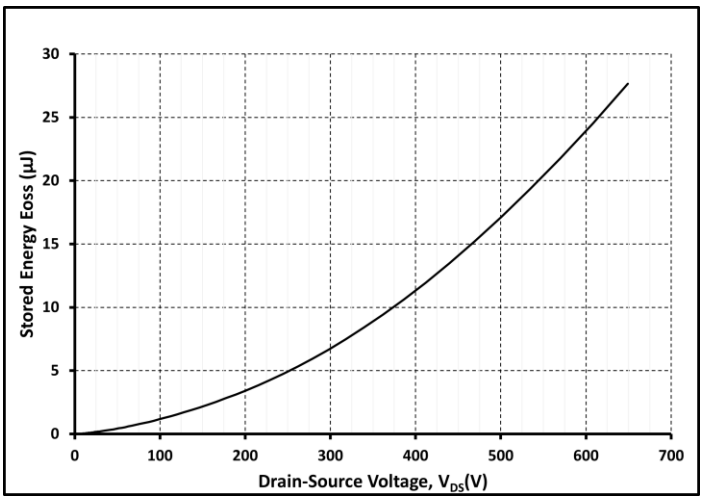


Fig. 17 Output Capacitor Stored Energy

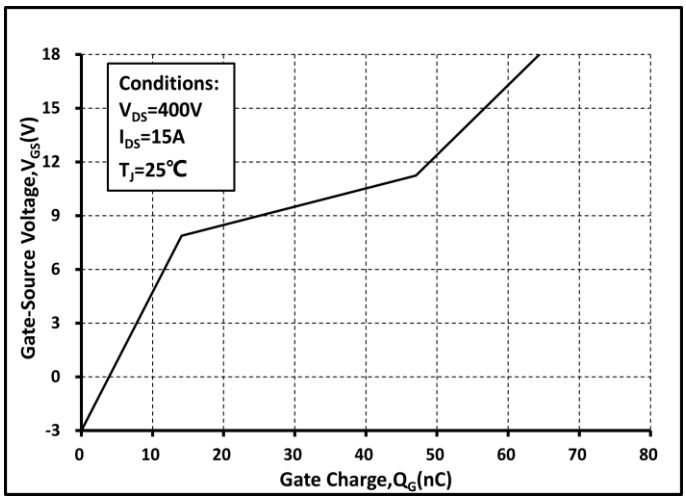


Fig. 18 Gate Charge Characteristics

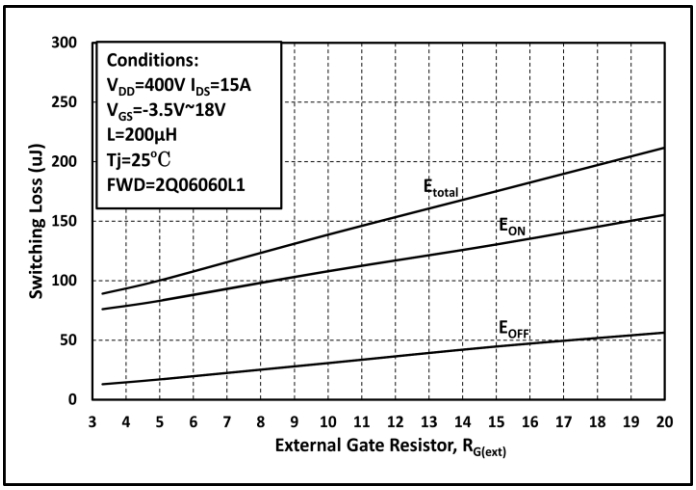


Fig. 19 Switching Energy vs. $R_{G(ext)}$

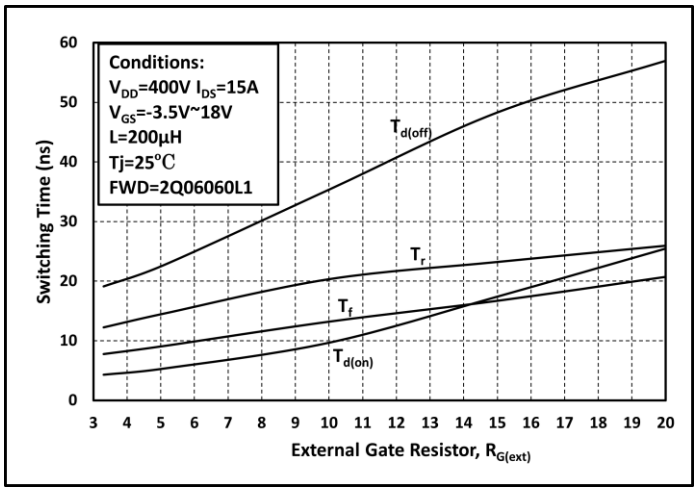


Fig. 20 Switching Times vs. $R_{G(ext)}$

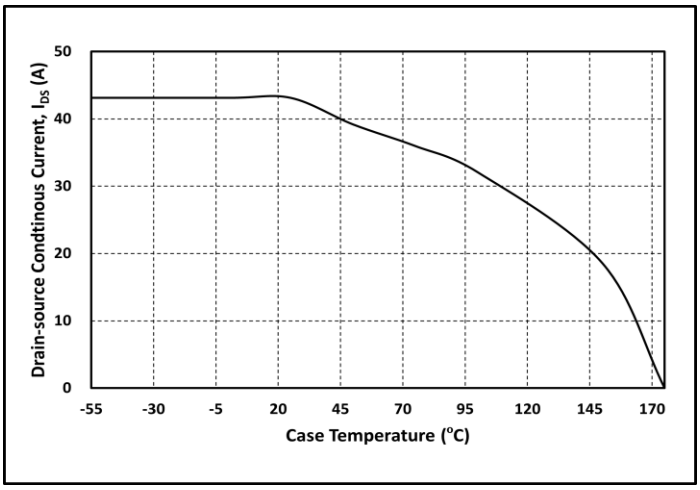


Fig. 21 Continuous Drain Current vs. Case Temperature

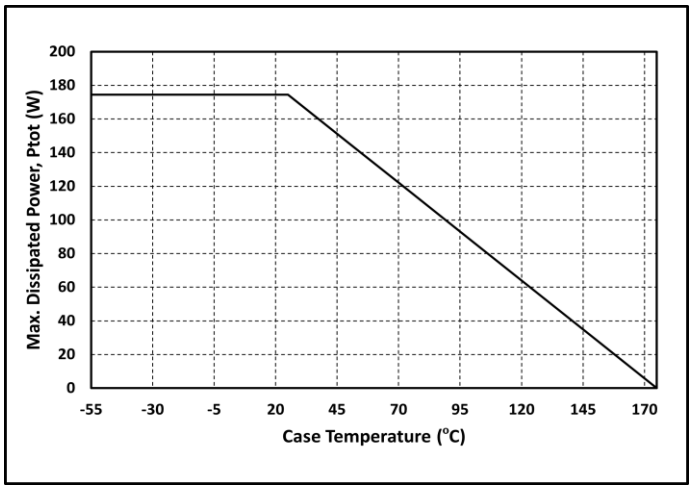


Fig. 22 Max. Power Dissipation Derating vs. Case Temperature

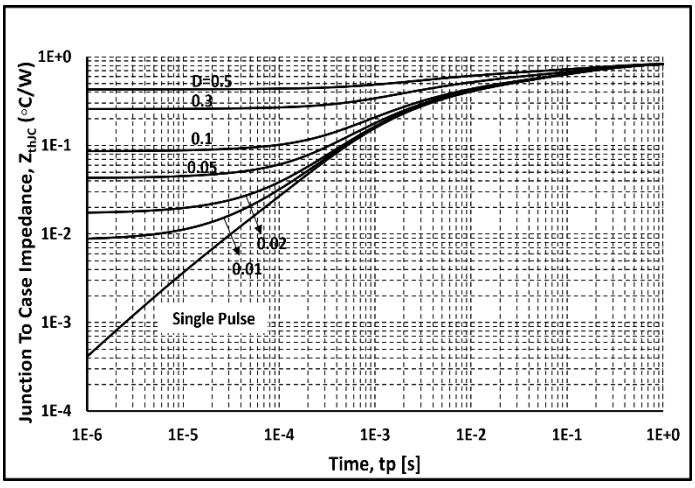


Fig. 23 Thermal impedance

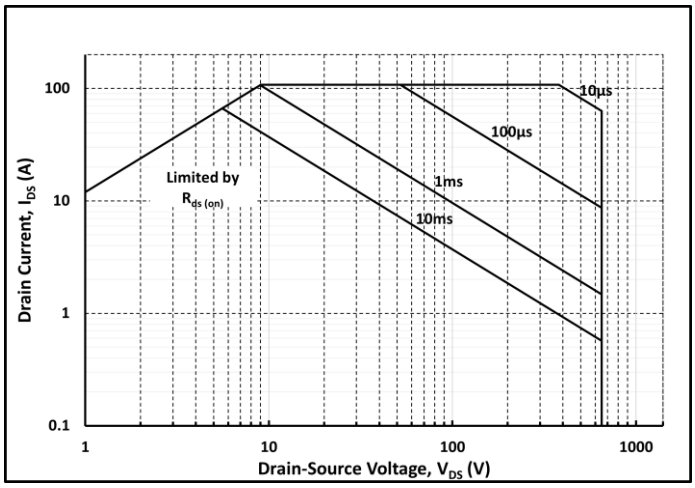
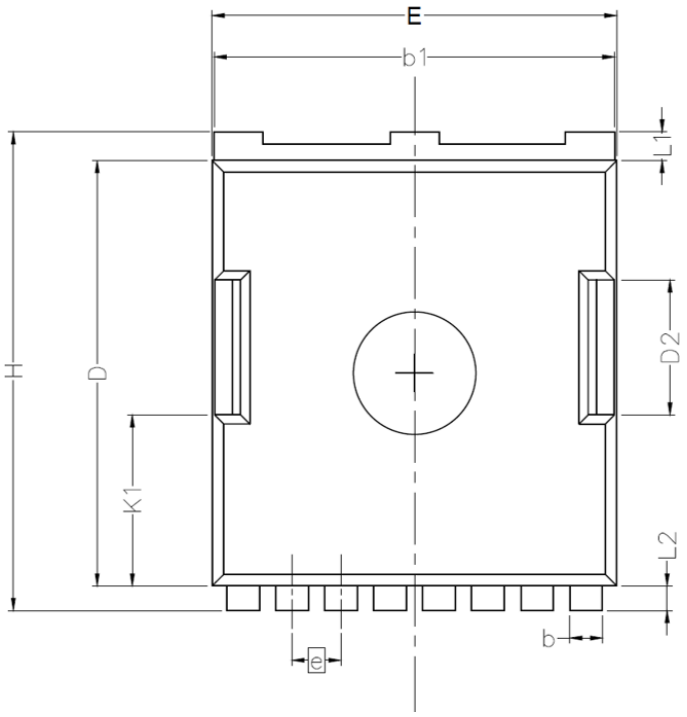
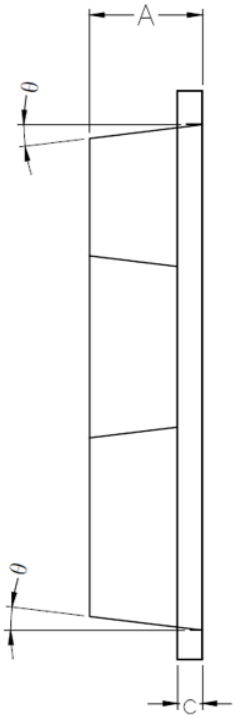


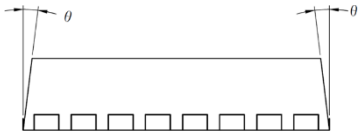
Fig. 24 Safe Operating Area

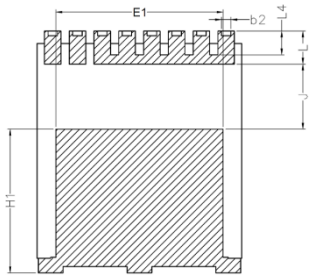
Package Dimensions



Dimensions In Millimeters		
SYMBOL	MIN.	MAX.
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.7	10.10
E1	7.90	8.30
e	1.20 BSC	
H	11.48	11.88
H1	6.75	7.15
N	8	
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4	1.00	1.30
θ	4°	10°







Note:

1. Package Reference: JEDEC TOLL, Variation AD
2. All Dimensions are in mm
3. Slot Required, Notch May Be Rounded
4. Dimension D&E Do Not Include Mold Flash
5. Subject to Change Without Notice

Notes

For further information please contact IVCT's office.

The Information in this document is subject to change without notice.

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